

Features

- 1.2kV Schottky Rectifier
- Zero Reverse Recovery Current
- High-Frequency Operation
- Temperature-Independent Switching
- Extremely Fast Switching

Benefits

- Replace Bipolar with Unipolar Rectifiers
- Essentially No Switching Losses
- Higher Efficiency
- Reduction of Heat Sink Requirements
- Parallel Devices Without Thermal Runaway

Applications

- Switch Mode Power Supplies (SMPS)
- Boost diodes in PFC or DC/DC stages
- Free Wheeling Diodes in Inverter stages
- AC/DC converters



Part Number	Packag	Qty(PCS)		
HFFSH40120ADNF085	TO247-3L	30		

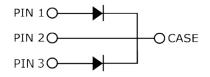
Maximum Ratings (Tc=25°C unless otherwise specified)

Symbol	Parameter	Value	Unit	Test Conditions	Note	
V _{RRM}	Repetitive Peak Reverse Voltage	1200	v			
V _{RSM}	Surge Peak Reverse Voltage	1300	V			
V _R	DC Peak Reverse Voltage	1200	V			
I _F	Continuous Forward Current (Per Leg/Device)	56.5/113 27/54 20/40	А	T _c =25°C T _c =135°C T _c =150°C	Fig. 3	
I _{FRM}	Repetitive Peak Forward Surge Current	91* 61*	А	T _c =25°C, t _p =10 ms, Half Sine Pulse T _c =110°C, t _p =10 ms, Half Sine Pulse		
I _{FSM}	Non-Repetitive Forward Surge Current	130* 110*	А	T _c =25°C, t _p =10 ms, Half Sine Pulse T _c =110°C, t _p =10 ms, Half Sine Pulse	Fig. 8	
I _{F,Max}	Non-Repetitive Peak Forward Current	1150* 950*	A	T _c =25°C, t _p =10 ms, Pulse T _c =110°C, t _p =10 ms, Pulse	Fig. 8	
P _{tot}	Power Dissipation (Per Leg/Device)	266/532 114/228	w	T _c =25°C T _c =110°C	Fig. 4	
dV/dt	Diode dV/dt ruggedness	200	V/ns	V _R =0-960V		
∫i²dt	i²t value	84.5* 60.5*	A²s	T _c =25°C, t _p =10 ms T _c =110°C, t _p =10 ms		
T,	Operating Junction Range	-55 to +175	°C			
T _{stg}	Storage Temperature Range	-55 to +135	°C			
	TO-247 Mounting Torque	1 8.8	Nm Ibf-in	M3 Screw 6-32 Screw		

* Per Leg, ** Per Device



TO247-3L Package



Shenzhen HuaXuanYang Electronics CO.,LTD
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Silicon Carbide Schottky Diode



Electrical Characteristics (Per Leg)

Symbol	Parameter	Тур.	Max.	Unit	Test Conditions	Note
$V_{\rm F}$	Forward Voltage	1.5 2.2	1.8 3	V	I _F = 20 A T _J =25°C I _F = 20 A T _J =175°C	Fig. 1
I _R	Reverse Current	35 65	200 400	μA	V _R = 1200 V T _J =25°C V _R = 1200 V T _J =175°C	Fig. 2
Q _c	Total Capacitive Charge	99		nC	V _R = 800 V, I _F = 20A di/dt = 200 A/μs T _J = 25°C	Fig. 5
С	Total Capacitance	1500 93 67		pF	V _R = 0 V, T _J = 25°C, f = 1 MHz V _R = 400 V, T _J = 25°C, f = 1 MHz V _R = 800 V, T _J = 25°C, f = 1 MHz	Fig. 6
Ec	Capacitance Stored Energy	28		μJ	V _R = 800 V	Fig. 7

Note: This is a majority carrier diode, so there is no reverse recovery charge.

Thermal Characteristics

Symbol	Parameter	Тур.	Unit	Note
R _{ejc}	Thermal Resistance from Junction to Case	0.29** 0.57*	°C/W	Fig. 9

* Per Leg, ** Per Device

Typical Performance (Per Leg)

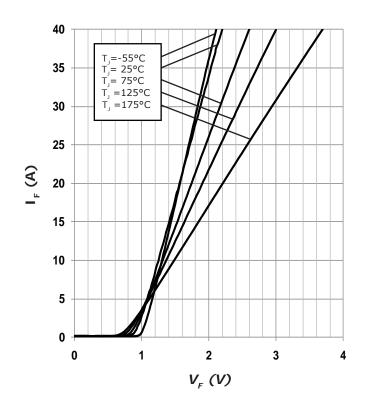


Figure 1. Forward Characteristics

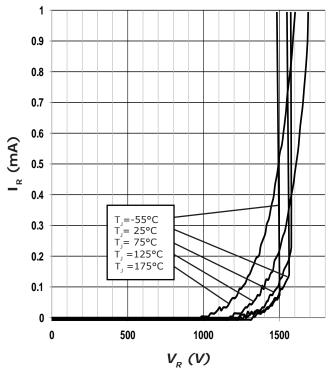
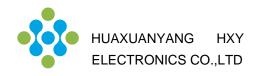
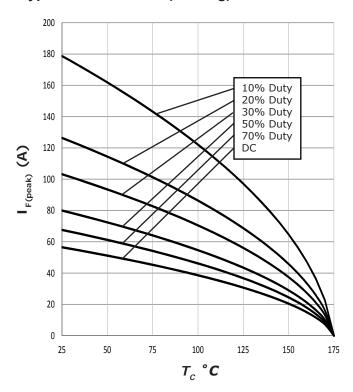


Figure 2. Reverse Characteristics

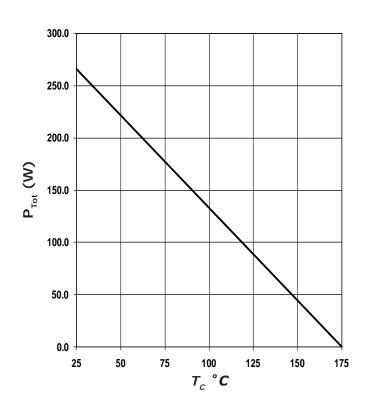


Typical Performance (Per Leg)





Q_c (nc)





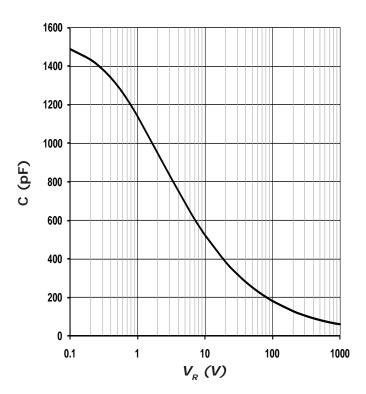
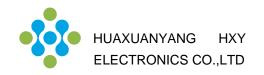


Figure 6. Capacitance vs. Reverse Voltage

Figure 5. Recovery Charge vs. Reverse Voltage

 V_{R} (V)



Typical Performance

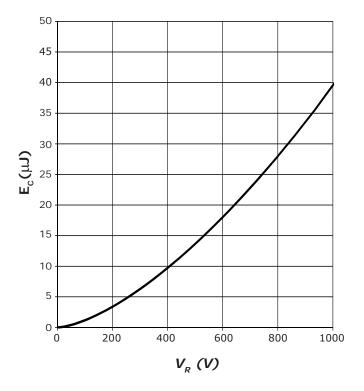


Figure 7. Typical Capacitance Stored Energy, per leg

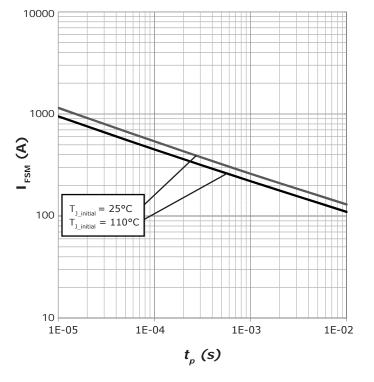


Figure 8. Non-Repetitive Peak Forward Surge Current versus Pulse Duration (sinusoidal waveform), per leg

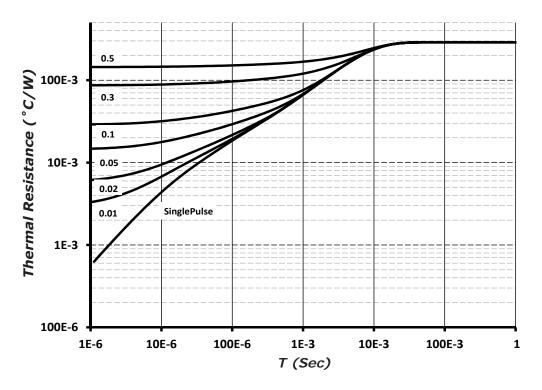
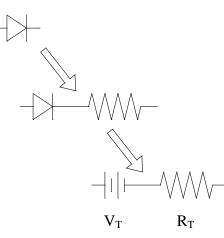


Figure 9. Device Transient Thermal Impedance



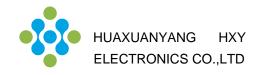
Diode Model



$$V_{fT} = V_T + If^*R_T$$

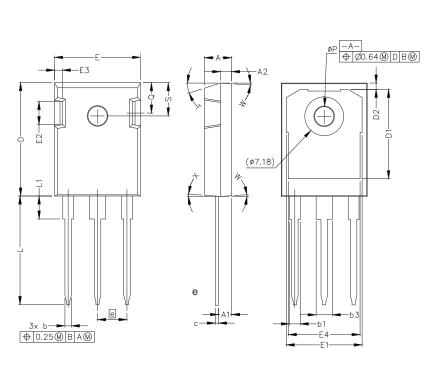
 $V_T = 0.97 + (T_J^* - 1.40^*10^{-3})$
 $R_T = 0.023 + (T_J^* 2.71^*10^{-4})$

Note: T_j = Diode Junction Temperature In Degrees Celsius, valid from 25°C to 175°C

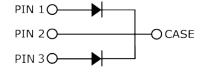


Package Dimensions

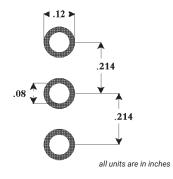
Package TO247-3L

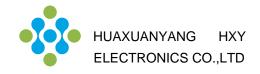


POS	Inc	hes	Millimeters		
P05	Min	Min Max		Max	
А	.190	.205	4.83	5.21	
A1	.090	.100	2.29	2.54	
A2	.075	.085	1.91	2.16	
b	.042	.052	1.07	1.33	
b1	.075	.095	1.91	2.41	
b3	.113	.133	2.87	3.38	
С	.022	.027	0.55	0.68	
D	.819	.831	20.80	21.10	
D1	.640	.695	16.25	17.65	
D2	.037	.049	0.95	1.25	
E	.620	.635	15.75	16.13	
E1	.516	.557	13.10	14.15	
E2	.145	.201	3.68	5.10	
E3	.039	.075	1.00	1.90	
E4	.487	.529	12.38	13.43	
е	.214	BSC	5.44 BSC		
L	.780	.800	19.81	20.32	
L1	.161	.173	4.10	4.40	
Ν	3				
ØP	.138	.144	3.51	3.65	
Q	.216	.236	5.49	6.00	
S	.238	.248	6.04	6.30	
Т	17.5° REF				
W	3.5° REF				
Х	4° REF				



Recommended Solder Pad Layout





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